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# DIODES, SILICON, FAST RECOVERY AVALANCHE RECTIFIERS, 400mW, BASED ON TYPES BYX57500 AND BYX57600 ESCC Detail Specification No. 5101/005

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# DIODES, SILICON, FAST RECOVERY AVALANCHE RECTIFIERS, 400mW, BASED ON TYPES BYX57500 AND BYX57600 ESA/SCC Detail Specification No. 5101/005

# space components coordination group

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Issue/Rev.		SCCG Chairman	ESA Director General or his Deputy	
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# DOCUMENTATION CHANGE NOTICE

Rev. Letter	Rev. Date	Reference	CHANGE Item	Approved DCR No.
1 1		This Issue superse Issue 3 and the follo Cover Page DCN Table of Contents Para. 1.4 Table 1(b) Para. 2 Para. 4.2.1 Para. 4.2.2 Para. 4.2.2 Para. 4.2.3 Para. 4.2.3 Para. 4.2.4 Para. 4.6 Para. 4.7.1 Para. 4.7.2 Para. 4.7.3 Para. 4.7.4 Table 2 D.C. Figure 4 Table 3	Item des Issue 3 and incorporates all modifications defined in wing DCR's:- : Amended as relevant : Text standardised : No. 4, symbol corrected : Reference to ESA/SCC Basic Scpecification No. 23500 added : Title corrected : PIND deviation entry standardised : H.T.R.B. entry deleted : Radiographic Inspection entry standardised : Title corrected : Title amended : Title amended : Third sentence standardised : Title and text standardised to include 'H.T.R.B. and Power' : Title and text standardised to include 'H.T.R.B. and Power'	None None 23476
		Figure 5 Para. 4.8.1 Para. 4.8.2 Para. 4.8.3 Para. 4.8.4	<ul> <li>corrected and attached to this Table</li> <li>Tables reversed in sequence</li> <li>First Title numbered "5(b)" and corrected</li> <li>Second Title numbered "5(a)" and corrected</li> <li>Figure Titles reversed in sequence</li> <li>Second sentence standardised</li> <li>Second sentence added</li> <li>Table reference amended to "5(b)"</li> <li>Figure reference amended to "5(b)"</li> </ul>	23476 23476 23476 23476 23476 23476 23476 23476 23476
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APPENDICES (Applicable to specific Manufacturers only)

None.



# 1. <u>GENERAL</u>

# 1.1 <u>SCOPE</u>

This specification details the ratings, physical and electrical characteristics, test and inspection data for a Silicon Fast Recovery Avalanche Rectifier Diode, 400mW, based on Types BYX57500 and BYX57600. It shall be read in conjunction with ESA/SCC Generic Specification No. 15000, the requirements of which are supplemented herein.

# 1.2 <u>COMPONENT TYPE VARIANTS</u>

Variants of the basic type diodes specified herein, which are also covered by this specification, are given in Table 1(a).

# 1.3 MAXIMUM RATINGS

The maximum ratings, which shall not be exceeded at any time during use or storage, applicable to the diodes specified herein, are as scheduled in Table 1(b).

# 1.4 PARAMETER DERATING INFORMATION

The parameter derating information applicable to the diodes specified herein, is shown in Figure 1.

# 1.5 PHYSICAL DIMENSIONS

The physical dimensions of the diodes specified herein, are shown in Figure 2.

# 1.6 FUNCTIONAL DIAGRAM

The functional diagram, showing lead identification, of the diodes specified herein, is shown in Figure 3.



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# TABLE 1(a) - TYPE VARIANTS

(1) VARIANT	(2) BASED ON TYPE	(3) V <sub>R</sub> (V)	(4) V <sub>(BR)</sub> MIN. (V)	(5) V <sub>(BR)</sub> MAX. (V)
01	BYX57500	500	540	750
02	BYX57600	600	720	950

# TABLE 1(b) - MAXIMUM RATINGS

No.	CHARACTERISTICS	SYMBOL	MAXIMUM RATING	UNIT	REMARKS
1	Breakdown Voltage	V <sub>BR</sub>	Note 1	V	-
2	DC Forward Current	lo	0.4	А	Note 2
3	Forward Surge Current	IFSM	3.0	А	$T_{amb} \le 25^{\circ}C$ $\Delta_l = 10ms$
4	Operating Temperature Range	Т <sub>ор</sub>	- 65 to + 125	°C	T <sub>amb</sub>
5	Storage Temperature Range	T <sub>stg</sub>	– 65 to + 150	°C	-
6	Soldering Temperature	T <sub>sol</sub>	+ 260	°C	Time: ≤10s; Distance to case: ≥1.5mm

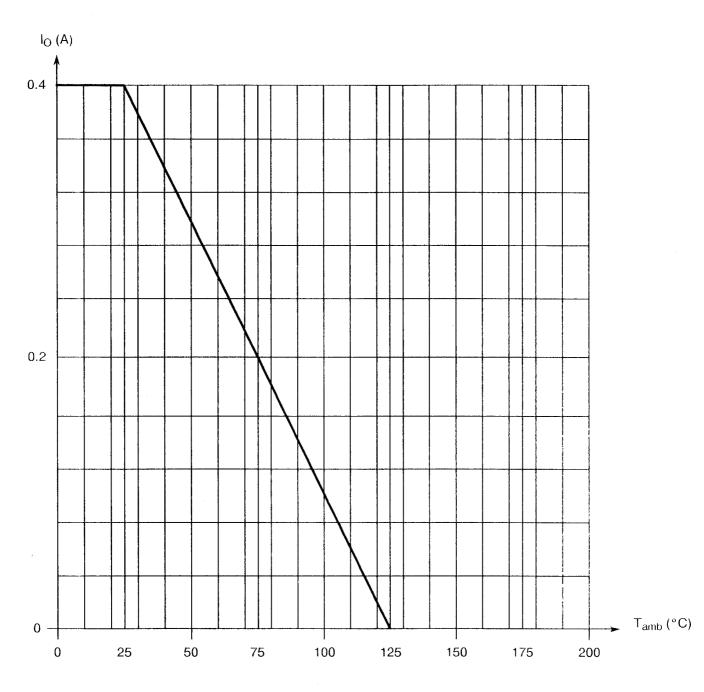
# **NOTES**

- 1. See Column (5) of Table 1(a).
- 2. At  $T_{amb} \leq$  + 25°C for derating with temperature see Figure 1.

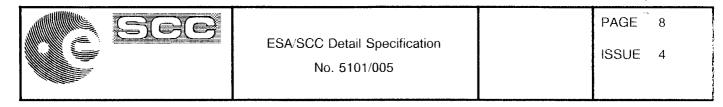


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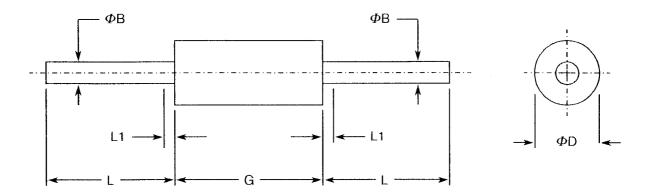




Average Output Current versus Temperature



# FIGURE 2 - PHYSICAL DIMENSIONS

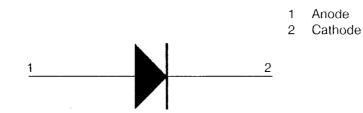


SYMBOL	MILLIM	ETRES	NOTES
STMBOL	MIN.	MAX.	NOTES
ФВ	0.458	0.558	-
ΦD	2.16	2.71	1
G	5.85	7.62	1
L	25.40	-	-
L1	-	1.27	2

#### **NOTES**

- 1. Package contour optional within cylinder of diameter  $\Phi D$  and length G. Slugs. if any, shall be included within this cylinder but shall not be subject to the minimum limit of  $\Phi D$ .
- 2. Lead diameter not controlled in this zone to allow for flash, lead finish build-up, and minor irregularities other than slugs.

# FIGURE 3 - FUNCTIONAL DIAGRAM



#### NOTES

1. The cathode end shall be marked with a coloured ring.



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#### 2. APPLICABLE DOCUMENTS

The following documents form part of this specification and shall be read in conjunction with it:-

- (a) ESA/SCC Generic Specification No. 5000 for Discrete Semiconductors.
- (b) MIL-STD-750, Test Methods and Procedures for Semiconductor Devices.
- (c) MIL-STD-202, Test Methods for Electronic and Electrical Component Parts.
- (d) ESA/SCC Basic Specification No. 23500, Requirements for Lead Materials and Finishes for Space Application.

#### 3. TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESA/SCC Basic Specification No. 21300 shall apply.

#### 4. **REQUIREMENTS**

#### 4.1 <u>GENERAL</u>

The complete requirements for procurement of the diodes specified herein shall be as stated in this specification and ESA/SCC Generic Specification No. 5000 for Discrete Semiconductors. Deviations from the Generic Specification, applicable to this Detail Specification only, are listed in Para. 4.2.

Deviations from the applicable Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESA/SCC requirements and do not affect the components' reliability, are listed in the appendices attached to this specification.

#### 4.2 DEVIATIONS FROM GENERIC SPECIFICATION

4.2.1 Deviations from Special In-process Controls

None.

#### 4.2.2 Deviations from Final Production Tests (Chart II)

- (a) Para. 9.2.1, Bond Strength Test: Shall not be performed.
- (b) Para. 9.2.2, Die Shear Test: Shall not be performed.
- (c) Para. 9.7, Particle Impact Noise Detection (PIND) Test: Not applicable.
- (d) Para. 9.5.1, Thermal Shock Test: Shall be performed in accordance with Test Method 107, Condition 'B' of MIL-STD-202.

#### 4.2.3 Deviations from Burn-in and Electrical Measurements (Chart III)

- (a) Para. 9.12, Radiographic Inspection: Not applicable.
- 4.2.4 Deviations from Qualification Tests (Chart IV)
  - (a) Para. 9.2.3, Bond Strength Test: Shall not be performed.
  - (b) Para. 9.2.4, Die Shear Test: Shall not be performed.
- 4.2.5 <u>Deviations from Lot Acceptance Tests (Chart V)</u> None.



#### 4.3 MECHANICAL REQUIREMENTS

#### 4.3.1 Dimension Check

The dimensions of the diodes specified herein shall be checked. They shall conform to those shown in Figure 2.

#### 4.3.2 Weight

The maximum weight of the diodes specified herein shall be 0.25 grammes.

#### 4.3.3 <u>Terminal Strength</u>

The requirements for terminal strength testing are specified in Section 9 of ESA/SCC Generic Specification No. 5000. The test conditions shall be as follows:-

Test Condition : 'A'.

Applied Force : 5.0 Newtons.

Duration : 10 seconds.

#### 4.4 MATERIALS AND FINISHES

The materials and finishes shall be as specified herein. Where a definite material is not specified, a material which will enable the diodes specified herein to meet the performance requirements of this specification shall be used. Acceptance or approval of any constituent material does not guarantee acceptance of the finished product.

4.4.1 <u>Case</u>

Glass, hermetically sealed.

#### 4.4.2 Lead Material and Finish

The lead material shall be Type 'C' with Type '3' or Type '4' finish in accordance with the requirements of ESA/SCC Basic Specification No. 23500.

# 4.5 <u>MARKING</u>

#### 4.5.1 <u>General</u>

The marking of all components delivered to this specification shall be in accordance with the requirements of ESA/SCC Basic Specification No. 21700. Each component shall be marked in respect of:-

- (a) Lead Identification.
- (b) The SCC Component Number.
- (c) Traceability Information.

#### 4.5.2 Lead Identification

Lead identification shall be as shown in Figures 2 and 3.



#### 4.5.3 The SCC Component Number

Each component shall bear the SCC Component Number which shall be constituted and marked as follows:

	510100502B
Detail Specification Number	
Type Variant (see Table 1(a))	
Testing Level (B or C, as applicable)	

#### 4.5.4 Traceability Information

Each component shall be marked in respect of traceability information as defined in ESA/SCC Basic Specification No. 21700.

#### 4.5.5 Marking of Small Components

When it is considered that the component is too small to accommodate the marking as specified above, as much as space permits shall be marked. The order of precedence shall be as follows:-

- (a) Lead identification.
- (b) The SCC Component number.
- (c) Traceability information.

The marking information in full shall accompany each component in its primary package.

#### 4.6 ELECTRICAL MEASUREMENTS

#### 4.6.1 Electrical Measurements at Room Temperature

The parameters to be measured at room temperature are scheduled in Table 2. The measurements shall be performed at  $T_{amb}$  = +22±3 °C.

#### 4.6.2 Electrical Measurements at High and Low Temperatures

The parameters to be measured at high and low temperatures are scheduled in Table 3.

#### 4.6.3 <u>Circuits for Electrical Measurements</u>

Circuits for use in performing electrical measurements listed in Tables 2 and 3 are shown in Figure 4.

#### 4.7 BURN-IN TESTS

#### 4.7.1 Parameter Drift Values

The parameter drift values applicable to burn-in are specified in Table 4 of this specification. Unless otherwise stated, measurements shall be performed at  $T_{amb} = +22 \pm 3$  °C. The parameter drift values ( $\Delta$ ) applicable to the scheduled parameters shall not be exceeded. In addition to these drift value requirements for a given parameter, the appropriate limit value specified in Table 2 shall not be exceeded.

#### 4.7.2 Conditions for H.T.R.B. and Power Burn-in

The requirements for H.T.R.B. and Power Burn-in are specified in Section 7 of ESA/SCC Generic Specification No. 5000. The conditions for H.T.R.B. and Power Burn-in shall be as specified in Tables 5(a) and 5(b) of this specification.

#### 4.7.3 Electrical Circuits for H.T.R.B. and Power Burn-in

Circuits for use in performing the H.T.R.B. and Power Burn-in tests are shown in Figures 5(a) and 5(b) of this specification.



# TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - D.C. PARAMETERS

No.	CHARACTERISTICS	SYMBOL	MIL-STD-750	TEST	LIMITS		UNIT
NO.	CIARACTERISTICS	UTWIDUL	TEST METHOD	CONDITIONS	MIN.	MAX.	UNIT
1	DC Forward Voltage	V <sub>F</sub>	4011	$I_F = I_O = 0.4A$	-	1.0	V
2	DC Reverse Current	۱ <sub>R</sub>	4016	$V_{R} = (1)V$	-	2.0	μΑ
3	DC Breakdown Voltage	V <sub>(BR)</sub>	4021	I <sub>R</sub> = 0.1mA	(2)	(3)	V

#### NOTES

- 1. See Column (3) of Table 1(a).
- 2. See Column (4) of Table 1(a).
- 3. See Column (5) of Table 1(a).

## TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - A.C. PARAMETERS

No. CHARACTERIST	CHARACTERISTICS	S SVMRAL	MIL-STD-750	TEST	LIMITS		UNIT
100.		UTIMBUL	TEST METHOD	CONDITIONS	MIN.	MAX.	UNIT
4	Reverse Current Recovery Time	t <sub>rr</sub>	4031	l <sub>F</sub> = 100mA l <sub>R</sub> = 100mA i <sub>rr</sub> = 50mA	-	200	ns



# TABLE 3 - ELECTRICAL MEASUREMENTS AT HIGH AND LOW TEMPERATURES

Nc	Nia	. CHARACTERISTICS	SYMBOL	MIL-STD-750 TEST METHOD	TEST CONDITIONS	LIMITS		UNIT
	NU.					MIN.	MAX.	UNIT
	2	DC Reverse Current	I <sub>R</sub>	4016	$T_{amb} = +100 ^{\circ}\text{C}$ $V_{R} = (1)V$	-	100	μΑ

## **NOTES**

1. See column (3) of Table 1(a).

# FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS

Not applicable

# TABLE 4 - PARAMETER DRIFT VALUES

No.	CHARACTERISTICS	SYMBOL	SPEC. AND/OR TEST METHOD	TEST CONDITIONS	CHANGE LIMITS	UNIT
1	DC Forward Voltage	V <sub>F</sub>	As per Table 2	As per Table 2	± 100 or (1) ± 10	mV %
2	DC Reverse Current	l <sub>R</sub>	As per Table 2	As per Table 2	± 500 or (1) ± 100	nA %

#### **NOTES**

1. Whichever is the greater.



# TABLE 5(a) - CONDITIONS FOR HIGH TEMPERATURE REVERSE BIAS BURN-IN

No.	CHARACTERISTICS	SYMBOL	CONDITION	UNIT	
1	Ambient Temperature	T <sub>amb</sub>	+ 125 (Note 1)	°C	
2	Reverse Voltage	V <sub>R</sub>	Note 2	V	
3	Duration	t	72	Hrs	

#### NOTES

1. At the end of the H.T.R.B. Burn-in,  $T_{amb}$  shall be decreased to room temperature and the reverse-bias shall remain applied until  $T_{amb}$  is less than +35°C.

2. See column (2) of Table 1(a).

#### TABLE 5(b) - CONDITIONS FOR POWER BURN-IN AND OPERATING LIFE TEST

No.	CHARACTERISTICS	SYMBOL	CONDITION	UNIT	
1	Forward Current	۱۴	400	mA	
2	Ambient Temperature	T <sub>amb</sub>	+ 25	°C	

#### FIGURE 5(a) - ELECTRICAL CIRCUIT FOR HIGH TEMPERATURE REVERSE BIAS BURN-IN

Not applicable.

# FIGURE 5(b) - ELECTRICAL CIRCUIT FOR POWER BURN-IN AND OPERATING LIFE TEST

Not applicable.



#### 4.8 <u>ENVIRONMENTAL AND ENDURANCE TESTS (CHARTS IV AND V OF ESA/SCC GENERIC</u> <u>SPECIFICATION NO. 5000)</u>

#### 4.8.1 <u>Electrical Measurements on Completion of Environmental Tests</u>

The parameters to be measured on completion of environmental tests are scheduled in Table 2. Unless otherwise stated, the measurements shall be performed at  $T_{amb} = +22 \pm 3$  °C.

#### 4.8.2 <u>Electrical Measurements at Intermediate Points and on Completion of Endurance Tests</u>

The parameters to be measured at intermediate points and on completion of endurance tests are scheduled in Table 6. Unless otherwise stated, the measurements shall be performed at  $T_{amb} = +22 \pm 3$  °C.

#### 4.8.3 Conditions for Operating Life Tests (Part of Endurance Testing)

The requirements for operating life testing are specified in Section 9 of ESA/SCC Generic Specification No. 5000. The conditions for operating life testing shall be the same as specified in Table 5(b) for the burn-in test.

#### 4.8.4 Electrical Circuits for Operating Life Tests

The circuit to be used for performance of the operating life tests shall be the same as shown in Figure 5(b) for burn-in.

#### 4.8.5 Conditions for High Temperature Storage Test (Part of Endurance Testing)

The requirements for the high temperature storage test are specified in ESA/SCC Generic Specification No. 5000. The temperature to be applied shall be the maximum storage temperature specified in Table 1(b) of this specification.



# TABLE 6 - ELECTRICAL MEASUREMENTS AT INTERMEDIATE POINTS AND ON COMPLETION OF ENDURANCE TESTS

No.	CHARACTERISTICS	SYMBOL	SPEC. AND/OR	TEST CONDITIONS	LIMITS		UNIT
140.			TEST METHOD		MIN.	MAX.	UNIT
1	DC Forward Voltage	V <sub>F</sub>	As per Table 2	As per Table 2	-	1.0	V
2	DC Reverse Current	l <sub>R</sub>	As per Table 2	As per Table 2	-	2.0	μA